

# Keisuke Yamamoto

## List of Publications by Year in descending order

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31  
papers

360  
citations

840776

11  
h-index

794594

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32  
all docs

32  
docs citations

32  
times ranked

285  
citing authors

#	ARTICLE	IF	CITATIONS
1	Sn Concentration Effects on Polycrystalline GeSn Thin Film Transistors. IEEE Electron Device Letters, 2021, 42, 1735-1738.	3.9	8
2	Isothermal Growth and Stacking Evolution in Highly Uniform Bernal-Stacked Bilayer Graphene. ACS Nano, 2020, 14, 6834-6844.	14.6	28
3	Interface trap and border trap characterization for Al <sub>2</sub> O <sub>3</sub> /GeO <sub>x</sub> /Ge gate stacks and influence of these traps on mobility of Ge p-MOSFET. AIP Advances, 2020, 10, 065119.	1.3	3
4	The Benefits of Using SiN as a Buried Oxide in Germanium-On-Insulator Substrate. , 2020, , .		0
5	Underlayer Selection to Improve the Performance of Polycrystalline Ge Thin Film Transistors. ECS Transactions, 2020, 98, 423-427.	0.5	2
6	(Invited) Border-Trap Characterization for Ge Gate Stacks with Thin GeOX layer Using Deep-Level Transient Spectroscopy. ECS Transactions, 2020, 98, 395-404.	0.5	0
7	Sn Doping Effects in Solid-Phase Crystallized Ge Thin-Film Transistors. ECS Meeting Abstracts, 2020, MA2020-02, 1353-1353.	0.0	0
8	Underlayer Selection to Improve the Performance of Polycrystalline Ge Thin Film Transistors. ECS Meeting Abstracts, 2020, MA2020-02, 1759-1759.	0.0	0
9	(Invited) Border-Trap Characterization for Ge Gate Stacks with Thin GeO <sub>x</sub> layer Using Deep-Level Transient Spectroscopy. ECS Meeting Abstracts, 2020, MA2020-02, 1754-1754.	0.0	0
10	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. Applied Physics Letters, 2019, 114, .	3.3	28
11	Ge field-effect transistor with asymmetric metal source/drain fabricated on Ge-on-Insulator: Schottky tunneling source mode operation and conventional mode operation. Japanese Journal of Applied Physics, 2019, 58, SBBA14.	1.5	0
12	Fabrication and characterization of asymmetric metal/Ge/metal diodes with Ge-on-insulator substrate. Japanese Journal of Applied Physics, 2019, 58, SBBE05.	1.5	1
13	SiN used as a Stressor in Germanium-On-Insulator Substrate. , 2019, , .		0
14	Two-step synthesis and characterization of vertically stacked SnS <sub>2</sub> and SnS <sub>2</sub> /MoS <sub>2</sub> p-n heterojunctions. Physical Chemistry Chemical Physics, 2018, 20, 889-897.	2.8	28
15	Border trap evaluation for SiO <sub>2</sub> /GeO <sub>2</sub> /Ge gate stacks using deep-level transient spectroscopy. Journal of Applied Physics, 2018, 124, .	2.5	8
16	Wide range control of Schottky barrier heights at metal/Ge interfaces with nitrogen-contained amorphous interlayers formed during ZrN sputter deposition. Semiconductor Science and Technology, 2018, 33, 114011.	2.0	1
17	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250°C. Journal of Applied Physics, 2018, 123, 215704.	2.5	24
18	Mechanism of mobility enhancement in Ge p-channel metal-oxide-semiconductor field-effect transistor due to introduction of Al atoms into SiO <sub>2</sub> /GeO <sub>2</sub> gate stack. Materials Science in Semiconductor Processing, 2017, 70, 246-253.	4.0	4

#	ARTICLE	IF	CITATIONS
19	Achievement of low parasitic resistance in Ge n-channel metal-oxide-semiconductor field-effect transistor using an embedded TiN-source/drain structure. <i>Semiconductor Science and Technology</i> , 2017, 32, 035001.	2.0	5
20	Fabrication of asymmetric Ge Schottky tunneling source n-channel field-effect transistor and its characterization of tunneling conduction. <i>Materials Science in Semiconductor Processing</i> , 2017, 70, 283-287.	4.0	4
21	Electrical and structural properties of group-4 transition-metal nitride (TiN, ZrN, and HfN) contacts on Ge. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	16
22	Electrical properties of pseudo-single-crystalline germanium thin-film-transistors fabricated on glass substrates. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	44
23	Fabrication of PtGe/Ge contacts with high on/off ratio and its application to metal source/drain Ge p-channel MOSFETs. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 070306.	1.5	10
24	Dramatic enhancement of low electric-field hole mobility in metal source/drain Ge p-channel metal-oxide-semiconductor field-effect transistors by introduction of Al and Hf into SiO <sub>2</sub> /GeO <sub>2</sub> gate stack. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	26
25	An accurate characterization of interface-state by deep-level transient spectroscopy for Ge metal-insulator-semiconductor capacitors with SiO <sub>2</sub> /GeO <sub>2</sub> bilayer passivation. <i>Journal of Applied Physics</i> , 2012, 112, 083707.	2.5	16
26	Postmetallization annealing effect of TiN-gate Ge metal-oxide-semiconductor capacitor with ultrathin SiO <sub>2</sub> /GeO <sub>2</sub> bilayer passivation. <i>Applied Physics Letters</i> , 2011, 98, 252102.	3.3	19
27	High-Performance Ge Metal-oxide-semiconductor Field-Effect Transistors with a Gate Stack Fabricated by Ultrathin SiO <sub>2</sub> /GeO <sub>2</sub> Bilayer Passivation. <i>Applied Physics Express</i> , 2011, 4, 051301.	2.4	23
28	Ohmic contact formation on n-type Ge by direct deposition of TiN. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	44
29	Thermodynamic evaluation of solidification structure of high chromium white cast iron. <i>International Journal of Cast Metals Research</i> , 2003, 16, 435-440.	1.0	5
30	A neural network prediction for the graphite nucleation and morphology in modified cast irons. <i>International Journal of Cast Metals Research</i> , 2001, 14, 157-164.	1.0	2
31	Expression of Prophenoloxidase mRNA during Silkworm Hemocyte Development. <i>Bioscience, Biotechnology and Biochemistry</i> , 2000, 64, 1197-1202.	1.3	9